# **UNR3113, UNR311T**

# Silicon PNP epitaxial planer transistor

### For digital circuit

#### ■ Features

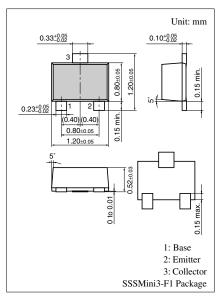
- Optimum for downsizing of the equipment and high-density mounting.
- Allowing automatic insertion through tape packing.

### ■ Resistance by Part Number

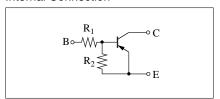
	Marking symbol	$(\mathbf{R}_1)$	$(R_2)$
• UNR3113	6C	$47~\text{k}\Omega$	$47~\mathrm{k}\Omega$
• UNR311T	EY	$22 \text{ k}\Omega$	$47~\mathrm{k}\Omega$

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-50	V
Collector to emitter voltage	$V_{CEO}$	-50	V
Collector current	$I_C$	-100	mA
Total power dissipation	$P_{T}$	100	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C



#### Internal Connection



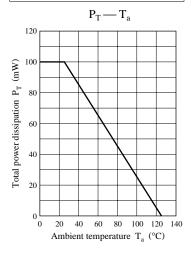
# ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parar	neter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff c	urrent	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
		I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	
Emitter cutoff	UNR3113	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			- 0.1	mA
current	UNR311T					- 0.2	
Collector to base	voltage	V <sub>CBO</sub>	$I_C = -10 \ \mu A, I_E = 0$	-50			V
Collector to emitt	er voltage	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Forward current	UNR3113	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	80			
stransfer ratio	UNR311T			80		400	
Collector to emitter	saturation voltage	V <sub>CE(sat)</sub>	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage hi	gh-level	V <sub>OH</sub>	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$		-4.9		V
Output voltage lo	w-level	V <sub>OL</sub>	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			- 0.2	V
	UNR3113		$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 1 \text{ k}\Omega$				

# $\blacksquare$ Electrical Characteristics (continued) $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

Parar	neter	Symbol	Conditions	Min	Тур	Max	Unit
Transition frequen	ncy	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Input resistance	UNR3113	R <sub>1</sub>		-30%	47	+30%	kΩ
	UNR311T				22		
Resistance ratio	UNR3113	R <sub>1</sub> /R <sub>2</sub>		0.8	1.0	1.2	
	UNR311T			0.37	0.47	0.57	

### Common characteristics chart



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